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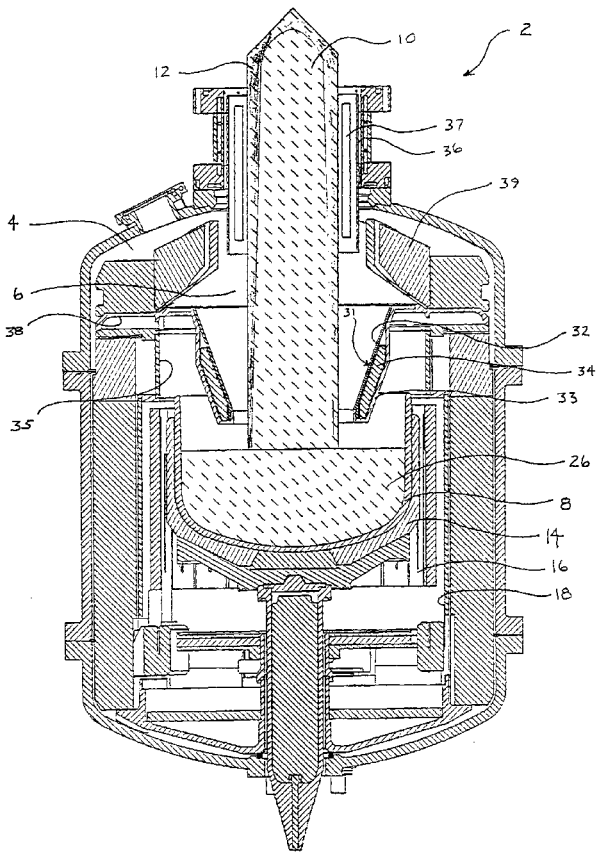
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(54) Title: APPARATUS AND PROCESS FOR THE PREPARATION OF LOW-IRON SINGLE CRYSTAL SILICON SUBSTANTIALLY FREE OF AGGLOMERATED INTRINSIC POINT DEFECTS



(57) Abstract: A method and apparatus for producing silicon single crystals with reduced iron contamination is disclosed. The apparatus contains at least one structural component constructed of a graphite substrate and a silicon carbide protective layer covering the surface of the substrate that is exposed to the atmosphere of the growth chamber. The graphite substrate has a concentration of iron no greater than about 1.5*1012 atoms/cm3 and the silicon carbide protective layer has a concentration of iron no greater than about 1.0*1012 atoms/cm3.

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